

# **Boost Chopper**

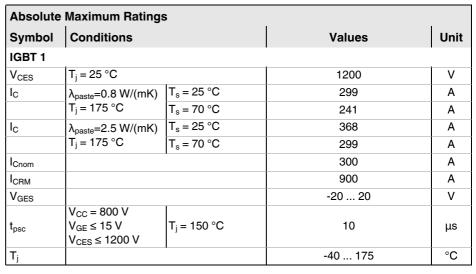
### SKiiP38GAL12E4V1

### Features\*

- Trench 4 IGBTs
- Robust and soft switching freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognized: File no. E63532
- NTC T-Sensor

#### Remarks

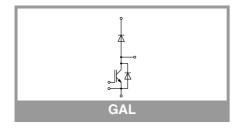
- Max. case temperature limited to T<sub>C</sub>=125°C
- Product reliability results valid for T<sub>j</sub>≤150°C (recommended T<sub>j,op</sub>=-40...+150°C)
   MiniSKiiP "Technical Explanations"
- MiniSKiiP "Technical Explanations" and "Mounting Instructions" are part of the data sheet. Please refer to both documents for further information.
- For storage and case temperature with TIM see document: "Technical Explanations Thermal Interface Materials"
- Diode 1 = D1
- Diode 2 = D2
- IGBT 1 = T2



Absolute Maximum Ratings							
Symbol	Conditions		Values	Unit			
Diode 1	•			•			
$V_{RRM}$	T <sub>j</sub> = 25 °C		1200	V			
I <sub>F</sub>	λ <sub>paste</sub> =0.8 W/(mK)	T <sub>s</sub> = 25 °C	274	Α			
	T <sub>j</sub> = 175 °C	T <sub>s</sub> = 70 °C	217	Α			
I <sub>F</sub>	λ <sub>paste</sub> =2.5 W/(mK)	T <sub>s</sub> = 25 °C	327	Α			
	T <sub>j</sub> = 175 °C	T <sub>s</sub> = 70 °C	260	Α			
I <sub>FRM</sub>			600	Α			
I <sub>FSM</sub>	10 ms	T <sub>j</sub> = 25 °C	1485	Α			
	sin 180°	T <sub>j</sub> = 150 °C	1485	Α			
T <sub>i</sub>			-40 175	°C			

Absolute Maximum Ratings							
Symbol	Conditions		Values	Unit			
Diode 2				•			
$V_{RRM}$	T <sub>j</sub> = 25 °C		1200	V			
I <sub>F</sub>	λ <sub>paste</sub> =0.8 W/(mK)	T <sub>s</sub> = 25 °C	17	Α			
	T <sub>j</sub> = 175 °C	T <sub>s</sub> = 70 °C	13	Α			
I <sub>F</sub>	λ <sub>paste</sub> =2.5 W/(mK)	T <sub>s</sub> = 25 °C	17	Α			
	T <sub>j</sub> = 175 °C	T <sub>s</sub> = 70 °C	14	Α			
I <sub>FRM</sub>			16	Α			
I <sub>FSM</sub>	10 ms	T <sub>j</sub> = 25 °C	36	Α			
	sin 180°	T <sub>j</sub> = 150 °C	36	Α			
Tj		,	-40 175	°C			

Absolute Maximum Ratings							
Symbol	Conditions	Values	Unit				
Module							
I <sub>t(RMS)</sub>	20 A per spring	280	Α				
T <sub>stg</sub>	module without TIM	-40 125	°C				
V <sub>isol</sub>	AC sinus 50 Hz, t = 1 min	2500	V				





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## SKiiP38GAL12E4V1

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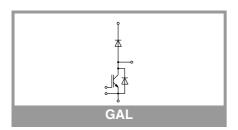
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Characteristics								
Symbol	Conditions		min.	typ.	max.	Unit		
IGBT 1								
V <sub>CE(sat)</sub>	I <sub>C</sub> = 300 A	T <sub>j</sub> = 25 °C		1.85	2.10	V		
	V <sub>GE</sub> = 15 V chiplevel	T <sub>j</sub> = 150 °C		2.25	2.45	V		
$V_{CE0}$	$ \begin{array}{c c} \textbf{I}_{C} = 300 \ \textbf{A} \\ \textbf{V}_{GE} = 15 \ \textbf{V} \\ \textbf{chiplevel} \\ \textbf{Chiplevel} \\ \textbf{V}_{GE} = 15 \ \textbf{V} \\ \textbf{chiplevel} \\ \textbf{V}_{GE} = 15 \ \textbf{V} \\ \textbf{Chiplevel} \\ \textbf{V}_{GE} = V_{CE}, \ \textbf{I}_{C} = 12 \\ \textbf{V}_{GE} = 0 \ \textbf{V}, \ \textbf{V}_{CE} = 13 \\ \textbf{V}_{CE} = 25 \ \textbf{V} \\ \textbf{V}_{GE} = 0 \ \textbf{V} \\ \textbf{V}_{GE} = 0 \ \textbf{V} \\ \textbf{V}_{GE} = 25 \ \textbf{V} \\ \textbf{V}_{GE} = 300 \ \textbf{A} \\ \textbf{V}_{GE} = 15 \ \textbf{V} \\ \textbf{V}_{GE} = 15 \ \textbf{V} \\ \textbf{V}_{GE} = 25 \ \textbf{V} \\ \textbf{V}_{GE} = 25 \ \textbf{V} \\ \textbf{V}_{GE} = 15 \ \textbf{V} \\ \textbf{V}_{GE} = 25 \ \textbf{V} \\ \textbf{V}_{GE} = 15 \ \textbf{V} \\ \textbf{V}_{GE} = 25 \ \textbf{V} \\ \textbf{V}_{GE} = 15 \ \textbf{V} \\ \textbf{V}_{GE} = 15 \ \textbf{V} \\ \textbf{V}_{GE} = 15 \ \textbf{V} \\ \textbf{V}_{GE} = 25 \ \textbf{V} \\ \textbf{V}_{GE} = 15 \ \textbf{V} \\ \textbf{V}_{GE} = 25 \ \textbf{V} \\ \textbf{V}_{GE} = 25 \ \textbf{V} \\ \textbf{V}_{GE} = 15 \ \textbf{V} \\ \textbf{V}_{GE} = 25 \ \textbf{N} \\ \textbf{V}_{GE} = 15 \ \textbf{V} \\ \textbf{V}_{GE} = 25 \ \textbf{N} \\ \textbf{V}_{GE} = 15 \ \textbf{V} \\ \textbf{V}_{GE} = 15 \ \textbf{V} \\ \textbf{V}_{GE} = 25 \ \textbf{N} \\ \textbf{V}_{GE} = 15 \ \textbf{V} \\ \textbf{V}_{GE} = 15 \ \textbf{V} \\ \textbf{V}_{GE} = 25 \ \textbf{N} \\ \textbf{V}_{GE} = 15 \ \textbf{V} \\ \textbf{V}_{GE} = 15 \ \textbf{V} \\ \textbf{V}_{GE} = 25 \ \textbf{N} \\ \textbf{V}_{GE} = 15 \ \textbf{V} \\ \textbf{V}_{GE} = 15 \ \textbf{V}_{GE} = 15 \ \textbf{V} \\ \textbf{V}_{GE} = 15 \ \textbf{V}_{GE} = 15 \ \textbf{V} \\ \textbf{V}_{GE} = 15 \ \textbf{V}_{GE} = 15 \ V$	T <sub>j</sub> = 25 °C		0.80	0.90	V		
		T <sub>j</sub> = 150 °C		0.70	0.80	V		
r <sub>CE</sub>	V <sub>GE</sub> = 15 V	T <sub>j</sub> = 25 °C		3.5	4.0	mΩ		
	chiplevel	T <sub>j</sub> = 150 °C		5.2	5.5	mΩ		
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_{C} = 12 \text{ r}$	nA	5	5.8	6.5	V		
I <sub>CES</sub>	$V_{GE} = 0 \text{ V}, V_{CE} = 12$			3.0	mA			
C <sub>ies</sub>	$V_{GE} = 0 \text{ V}, V_{CE} = 1200$ $V_{CE} = 25 \text{ V}$ $V_{GE} = 0 \text{ V}$ $f$ $V_{GE} = -8 \text{ V}+ 15 \text{ V}$ $T_{j} = 25 ^{\circ}\text{C}$	f = 1 MHz		17.60		nF		
Coes		f = 1 MHz		1.16		nF		
C <sub>res</sub>		f = 1 MHz		0.94		nF		
$Q_{G}$	V <sub>GE</sub> = - 8 V+ 15 V			1700		nC		
R <sub>Gint</sub>	T <sub>j</sub> = 25 °C			2.5		Ω		
t <sub>d(on)</sub>		T <sub>j</sub> = 150 °C		180		ns		
t <sub>r</sub>	_	T <sub>j</sub> = 150 °C		51		ns		
E <sub>on</sub>		T <sub>j</sub> = 150 °C		19		mJ		
t <sub>d(off)</sub>		T <sub>j</sub> = 150 °C		455		ns		
t <sub>f</sub>	di/dt <sub>on</sub> = 6995 A/μs	T <sub>j</sub> = 150 °C		96		ns		
E <sub>off</sub>	dv/dt = 5280 V/μs	T <sub>j</sub> = 150 °C	34.6			mJ		
R <sub>th(j-s)</sub>	per IGBT, λ <sub>paste</sub> =0.8	3 W/(mK)		0.2		K/W		
R <sub>th(j-s)</sub>	per IGBT, λ <sub>paste</sub> =2.5	5 W/(mK)		0.14		K/W		

Characteristics								
Symbol	Conditions		min.	typ.	max.	Unit		
Diode 1						•		
V <sub>F</sub>	I <sub>F</sub> = 300 A	T <sub>j</sub> = 25 °C		2.20	2.52	V		
	V <sub>GE</sub> = 0 V chiplevel	T <sub>j</sub> = 150 °C		2.15	2.47	V		
$V_{F0}$	chiplevel	T <sub>j</sub> = 25 °C		1.30	1.50	V		
	Chipievei	T <sub>j</sub> = 150 °C		0.90	1.10	V		
r <sub>F</sub>	chiplevel	T <sub>j</sub> = 25 °C		3.0	3.4	mΩ		
	Chipievei	T <sub>j</sub> = 150 °C		4.2	4.6	mΩ		
I <sub>RRM</sub>	I <sub>F</sub> = 300 A	T <sub>j</sub> = 150 °C		353		Α		
Q <sub>rr</sub>	$di/dt_{off} = 7005 \text{ A/}\mu\text{s}$ $V_{GF} = -15 \text{ V}$	T <sub>j</sub> = 150 °C		49		μC		
Err	V <sub>GE</sub> = -15 V V <sub>CC</sub> = 600 V	T <sub>j</sub> = 150 °C		21.5		mJ		
R <sub>th(j-s)</sub>	per Diode, $\lambda_{paste}=0$ .	8 W/(mK)		0.25		K/W		
R <sub>th(j-s)</sub>	per Diode, $\lambda_{paste}$ =2.	5 W/(mK)		0.19		K/W		





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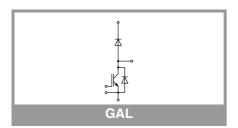
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Characteristics								
Symbol	Conditions		min.	typ.	max.	Unit		
Diode 2	•							
$V_{F}$	I <sub>F</sub> = 8 A	T <sub>j</sub> = 25 °C		2.33	2.65	٧		
	V <sub>GE</sub> = 0 V chiplevel	T <sub>j</sub> = 150 °C		2.35	2.68	V		
$V_{F0}$	chiplevel	T <sub>j</sub> = 25 °C		1.30	1.50	V		
	Chipievei	T <sub>j</sub> = 150 °C		0.90	1.10	V		
r <sub>F</sub>	chiplevel	T <sub>j</sub> = 25 °C		129	144	mΩ		
	Chipievei	T <sub>j</sub> = 150 °C		181	198	mΩ		
I <sub>RRM</sub>	I <sub>F</sub> = 8 A	T <sub>j</sub> = 150 °C		t.b.d.		Α		
Q <sub>rr</sub>	V <sub>GF</sub> = -15 V	T <sub>j</sub> = 150 °C		t.b.d.		μС		
E <sub>rr</sub>	$V_{CC} = 600 \text{ V}$	T <sub>j</sub> = 150 °C		t.b.d.		mJ		
R <sub>th(j-s)</sub>	per Diode, λ <sub>paste</sub> =0.8 W/(mK)			2.2		K/W		
R <sub>th(j-s)</sub>	per Diode, $\lambda_{paste}$	=2.5 W/(mK)		2		K/W		

Characteristics								
Symbol	Conditions	min.	typ.	max.	Unit			
Module								
Ms	to heat sink	2		2.5	Nm			
W	weight		82		g			

Characteristics								
Symbol	Conditions	min.	typ.	max.	Unit			
Temperature Sensor								
R <sub>100</sub>	T <sub>c</sub> =100°C (R <sub>25</sub> =5 kΩ)		Ω					
B <sub>25/85</sub>	$R_{(T)} = R_{25} * \exp[B_{25/85} * (1/T-1/298)], T[K]$	3420						



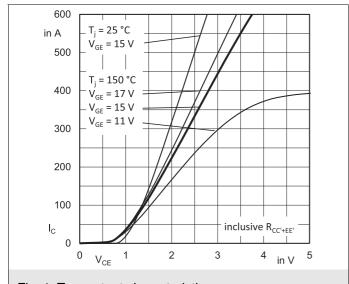


Fig. 1: Typ. output characteristic

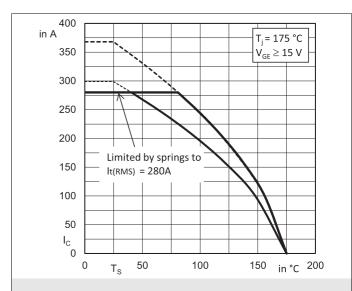


Fig. 2: Rated current vs. temperature  $I_C = f(T_S)$ 

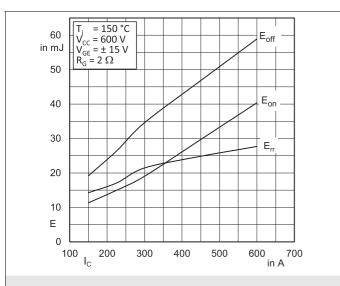


Fig. 3: Typ. turn-on /-off energy =  $f(I_C)$ 

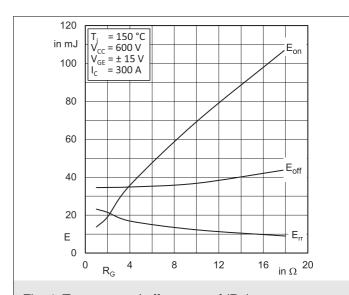


Fig. 4: Typ. turn-on /-off energy =  $f(R_G)$ 

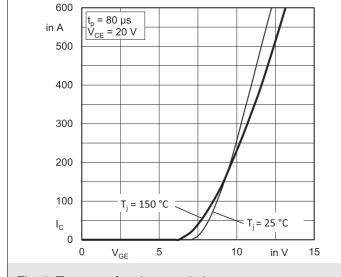


Fig. 5: Typ. transfer characteristic

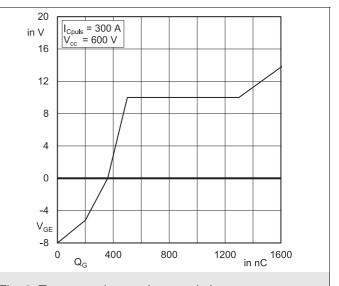
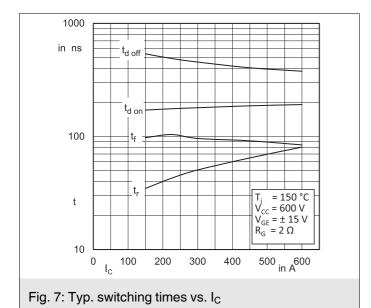


Fig. 6: Typ. gate charge characteristic



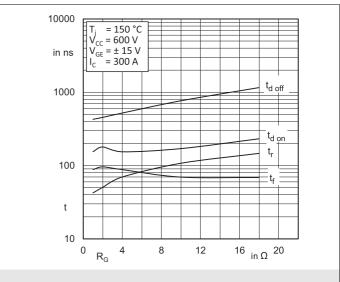
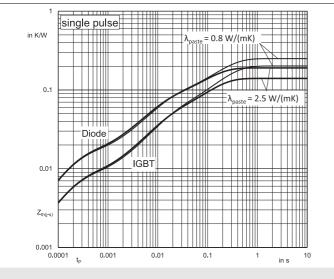


Fig. 8: Typ. switching times vs. gate resistor R<sub>G</sub>





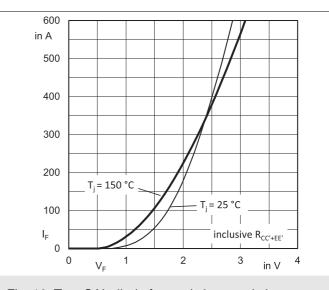


Fig. 10: Typ. CAL diode forward characteristic

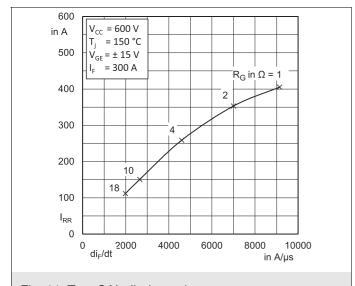


Fig. 11: Typ. CAL diode peak reverse recovery current

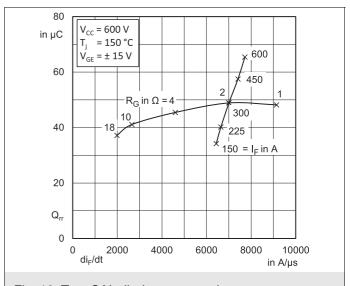
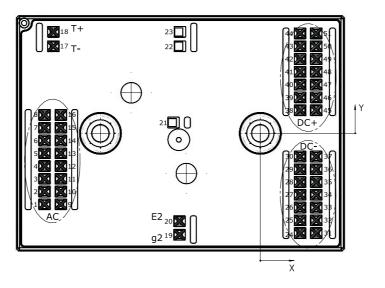


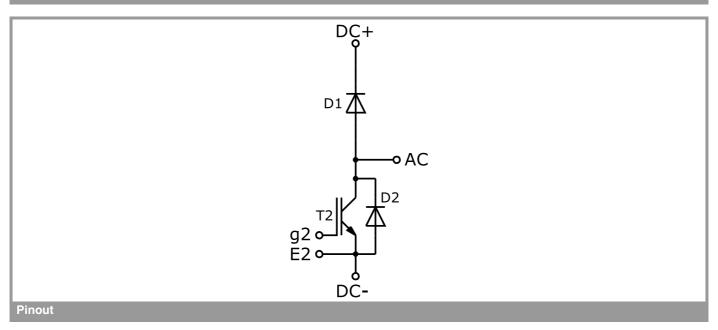
Fig. 12: Typ. CAL diode recovery charge

Pin out											
Pin	X	Υ	Function	Pin	X	Υ	Function	Pin	X	Υ	Function
1	-53,98	-17,80	AC	18	-51,78	25,40	T+	35	13,98	-12,20	DC-
2	-53,98	-14,60	AC	19	-20,23	-25,40	g2	36	13,98	-9,00	DC-
3	-53,98	-11,40	AC	20	-20,23	-22,00	E2	37	13,98	-5,80	DC-
4	<b>-</b> 53,98	<del>-</del> 8,20	AC	21	-21,73	2,70		38	9,93	5,80	DC+
5	<b>-</b> 53,98	-5,00	AC	22	-20,13	21,80		39	9,93	9,00	DC+
6	<b>-</b> 53,98	-1,80	AC	23	-20,13	25,40		40	9,93	12,20	DC+
7	<b>-</b> 53,98	1,40	AC	24	9,93	-25,00	DC-	41	9,93	15,40	DC+
8	<b>-</b> 53,98	4,60	AC	25	9,93	-21,80	DC-	42	9,93	18,60	DC+
9	<b>-</b> 49,93	-17,80	AC	26	9,93	-18,60	DC-	43	9,93	21,80	DC+
10	<b>-</b> 49,93	-14,60	AC	27	9,93	-15,40	DC-	44	9,93	25,00	DC+
11	<b>-</b> 49,93	-11,40	AC	28	9,93	-12,20	DC-	45	13,98	5,80	DC+
12	<b>-</b> 49,93	-8,20	AC	29	9,93	-9,00	DC-	46	13,98	9,00	DC+
13	<b>-</b> 49,93	-5,00	AC	30	9,93	<del>-</del> 5,80	DC-	47	13,98	12,20	DC+
14	-49,93	-1,80	AC	31	13,98	-25,00	DC-	48	13,98	15,40	DC+
15	-49,93	1,40	AC	32	13,98	-21,80	DC-	49	13,98	18,60	DC+
16	-49,93	4,60	AC	33	13,98	-18,60	DC-	50	13,98	21,80	DC+
17	-51,78	21,80	T-	34	13,98	-15,40	DC-	51	13,98	25,00	DC+

all values in [mm]



## **Pinout and Dimensions**



This is an electrostatic discharge sensitive device (ESDS) due to international standard IEC 61340.

#### \*IMPORTANT INFORMATION AND WARNINGS

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